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- (54) **Title:** CONFORMAL AND SELECTIVE SIN DEPOSITION

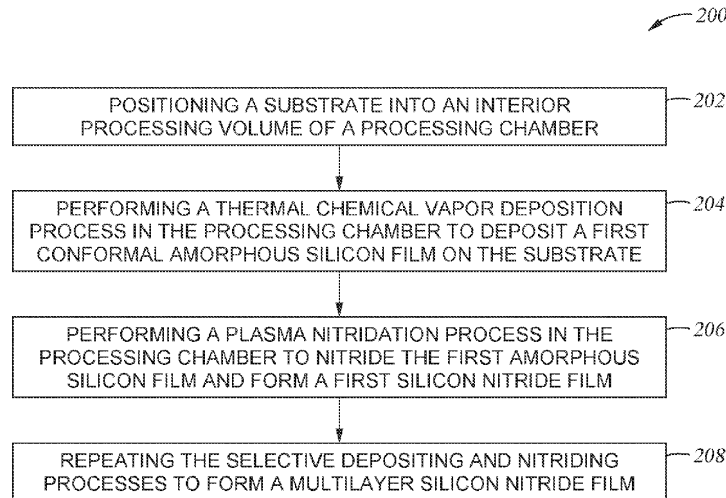


Fig. 2

- (57) **Abstract:** The present disclosure generally relates to methods for forming silicon nitride film layers on substrates. In an embodiment, the method includes positioning a substrate having at least one feature thereon in a process chamber, depositing a first silicon film layer on a non-silicon oxide surface of the substrate for a time duration of about 1 to about 4 minutes, nitriding the first silicon film layer to form a first silicon nitride film layer on the substrate, selectively depositing a second silicon film layer on the first silicon nitride film layer, and nitriding the second silicon film layer to form a second silicon nitride film layer disposed directly on the first silicon nitride film layer.

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